

SC180N75ZW

Silicon Carbide MOSFET 750V, 180mΩ, 18A



重庆平伟半导体股份有限公司

Features

- 0 V turn-off gate voltage can be applied
- High Blocking Voltage with Low RDS(on)
- High Speed Switching with Low Capacitances
- Easy to Parallel and Simple to Drive
- Qualified according to JEDEC criteria



100% DVDS Tested
100% Avalanche Tested

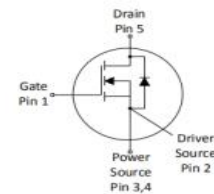
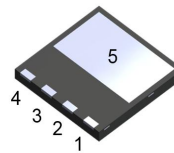
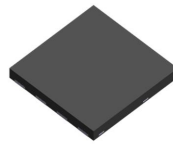
Applications

- Lighting
- Telecom and UPS
- PWM stages for e.g. PC Silverbox, Adapter, LCD & PDP TV

Product Summary

V_{DS}	750V
$R_{DS(on)}$ typ.	180mΩ
I_D	18A

DFN8*8



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
SC180N75ZW	SC180N75ZW	DFN8*8	Tape&Reel	13 inches	16mm	4000pcs

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	750	V
Continuous drain current $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$ (Silicon limit)	I_D	18 13	A
Pulsed drain current ($T_C = 25^\circ\text{C}$)	$I_{D \text{ pulse}}$	55	A
Avalanche energy, single pulse ($L=5\text{mH}$)	E_{AS}	16	mJ
Gate-Source voltage,max.transient voltage	V_{GSmax}	-8/+22	V
Recommended operating values	V_{GSsop}	0/+18	V
Power dissipation $T_C = 25^\circ\text{C}$	P_{tot}	65	W
Operating junction and storage temperature	T_j, T_{stg}	-55...+175	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Thermal resistance, junction – case.	R_{thJC}	-	1.3	2.3	°C/W	-
Thermal resistance, junction - ambient(min. footprint)	R_{thJA}	-	-	45	°C/W	1 inch ² , 2oz single copper FR-4 PCB.

Electrical Characteristic (at T_j = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV_{DSS}	750	-	-	V	$V_{GS}=0V, I_D=100\mu A$
Gate threshold voltage	$V_{GS(th)}$	2.5	3.5	4.5	V	$V_{DS}=V_{GS}, I_D=6mA$
Zero gate voltage drain current	I_{DSS}	-	1	10	μA	$V_{DS}=750V, V_{GS}=0V$ $T_j=25^\circ C$
		-	-	100		$T_j=175^\circ C$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS}=22V, V_{DS}=0V$
		-	-	-100	nA	$V_{GS}=-8V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	180	240	mΩ	$V_{GS}=15V, I_D=10A$
Drain-source on-state resistance	$R_{DS(on)}$	-	130	185	mΩ	$V_{GS}=18V, I_D=10A$
Transconductance	g_{fs}	-	6.5	-	S	$V_{DS}=20V, I_D=10A$

Dynamic Characteristic

Input Capacitance	C_{iss}	-	503	-	pF	$V_{GS}=0V, V_{DS}=400V,$ $f=1MHz$
Output Capacitance	C_{oss}	-	42	-		
Reverse Transfer Capacitance	C_{rss}	-	4	-		
Gate Total Charge	Q_G	-	17	-	nC	$V_{DS}=400V, I_D=10A$ $, V_{GS}=0V/15V$
Gate-Source charge	Q_{gs}	-	5	-		
Gate-Drain charge	Q_{gd}	-	8	-		
Turn-on delay time	$t_{d(on)}$	-	12	-	ns	$V_{GS}=0/18V, V_{DD}=400V,$ $R_G=5\Omega, I_D=10A$
Rise time	t_r	-	13	-		
Turn-off delay time	$t_{d(off)}$	-	22	-		
Fall time	t_f	-	7	-		
Gate resistance	R_G	-	3.0	-	Ω	$V_{GS}=0V, f=1MHz$

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Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	4.2	-	V	$V_{GS}=0V, I_{SD}=10A$ $T_j=25^{\circ}C$
		-	3.7	-		$T_j=175^{\circ}C$
Body Diode Continuous Forward Current	I_S	-	-	18	A	$T_C = 25^{\circ}C$
		-	-	13	A	$T_C = 100^{\circ}C$
Body Diode Reverse Recovery Time	t_{rr}	-	23	-	ns	$V_{GS}=-5V, I_{SD}=10A,$ $V_R=400V$ $di/dt=1000A/us$
Body Diode Reverse Recovery Charge	Q_{rr}	-	88	-	nC	
Peak Reverse Recovery Current	I_{RRM}	-	5	-	A	

Typical Performance Characteristics

Fig 1: Output Characteristics $T_j=25^{\circ}\text{C}$

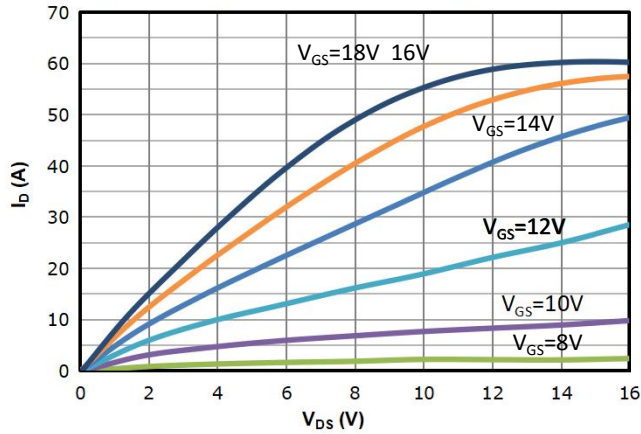


Fig 2: Output Characteristics $T_j=175^{\circ}\text{C}$

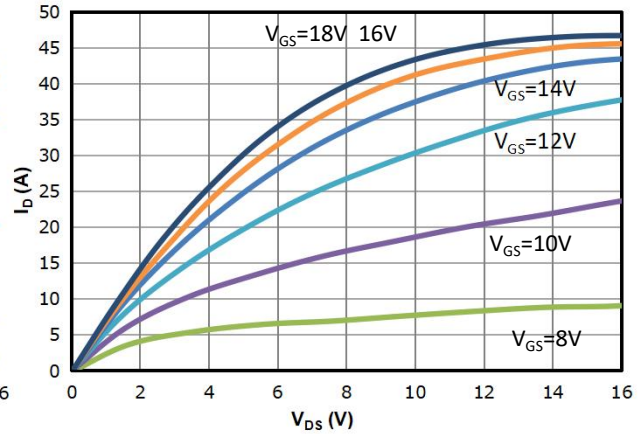


Fig 3: Transfer Characteristics

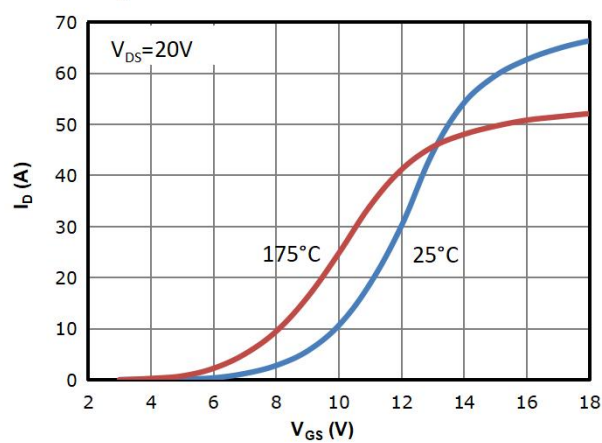


Fig 4: $R_{ds(on)}$ vs Drain Current and Gate Voltage

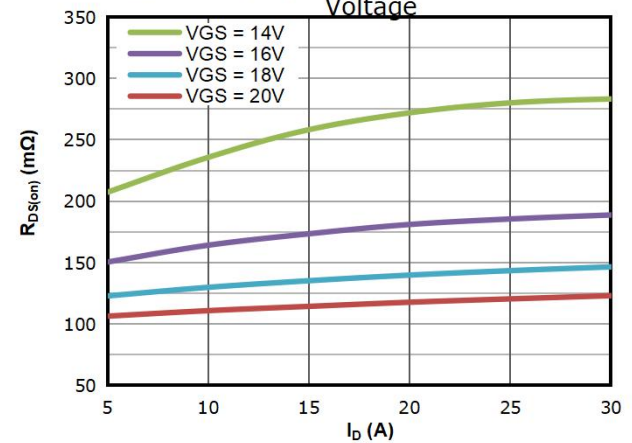


Fig 5: $R_{ds(on)}$ vs. Temperature

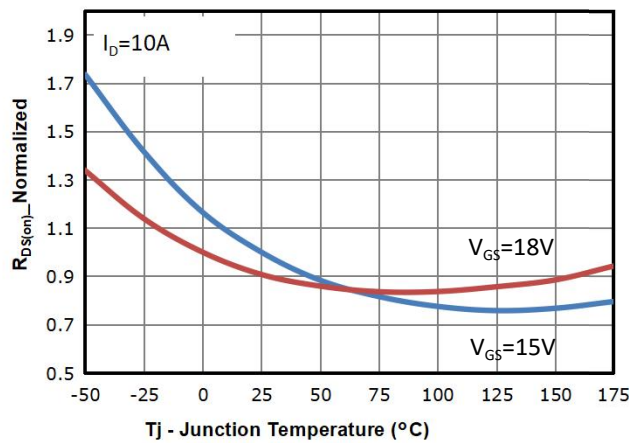


Fig 6: $V_{gs(th)}$ vs. Temperature

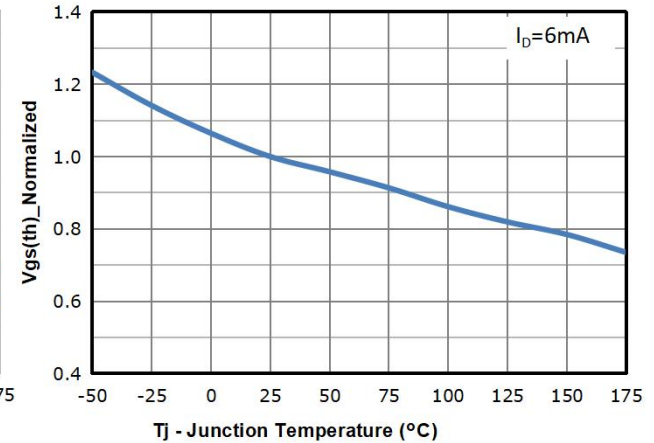


Fig 7: BVdss vs. Temperature

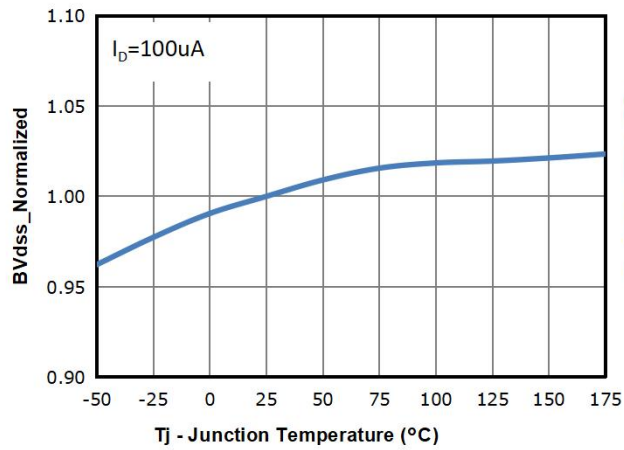


Fig 8: Capacitance Characteristics

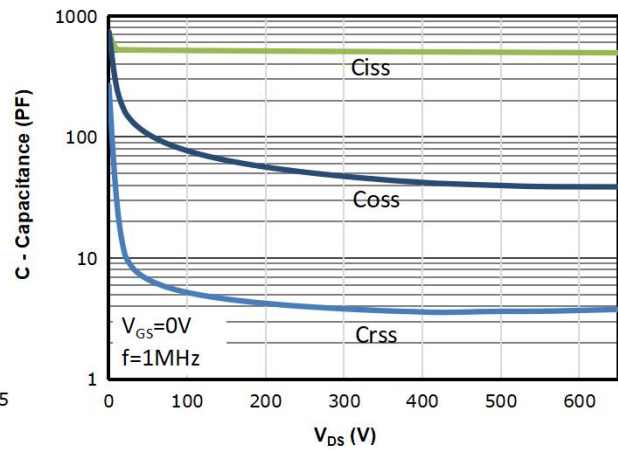


Fig 9: Gate Charge Characteristics

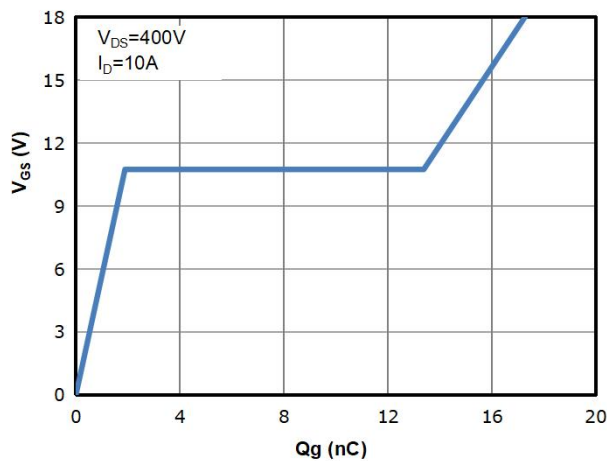


Fig 10: Body-diode Forward Characteristics

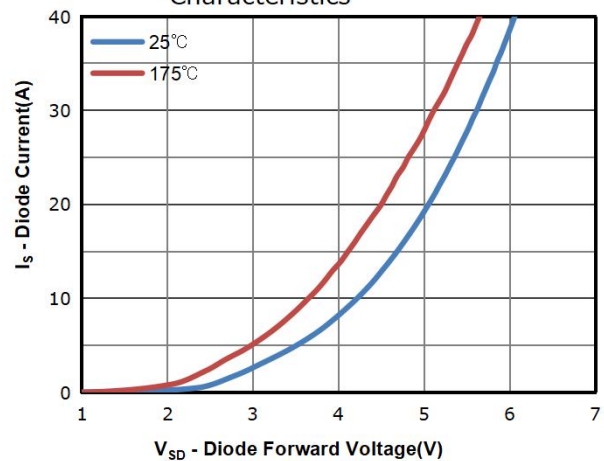


Fig 11: Power Dissipation

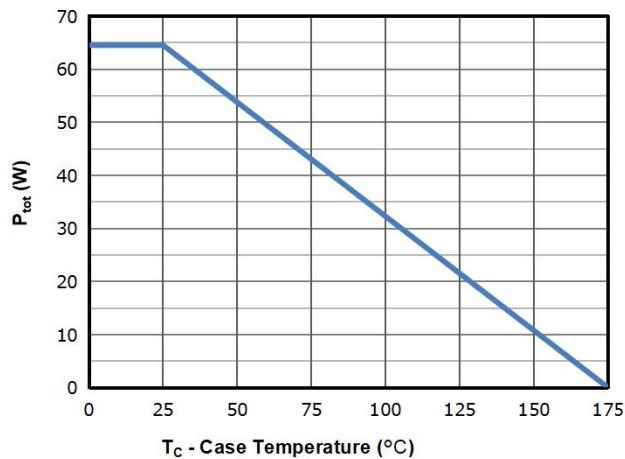
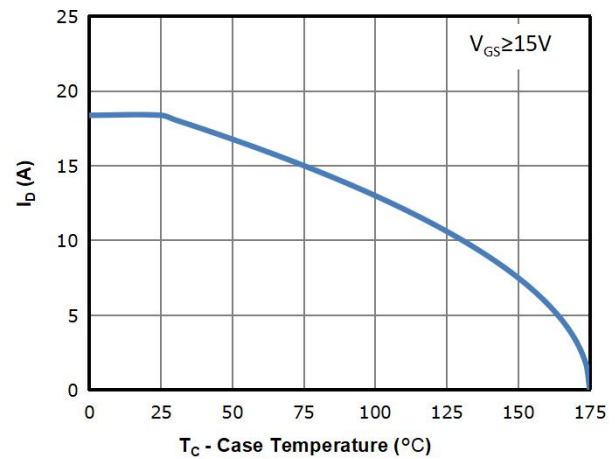


Fig 12: Drain Current Derating



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Fig 13: Safe Operating Area

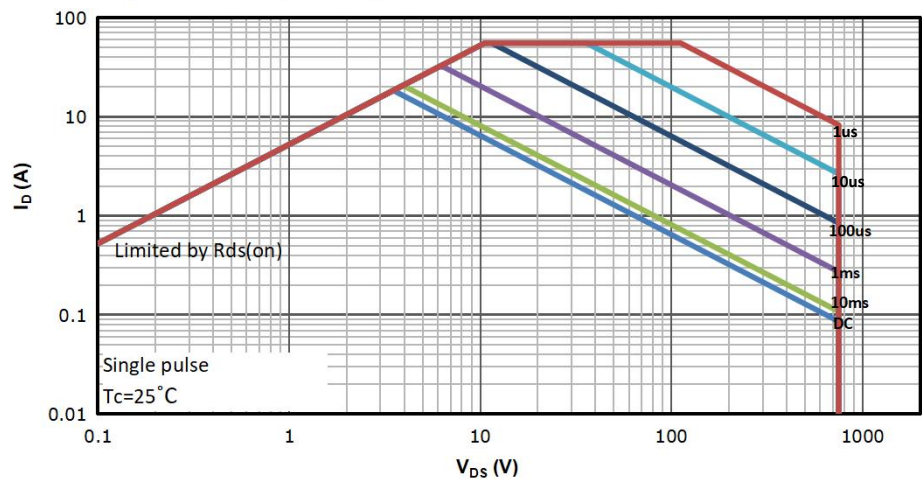
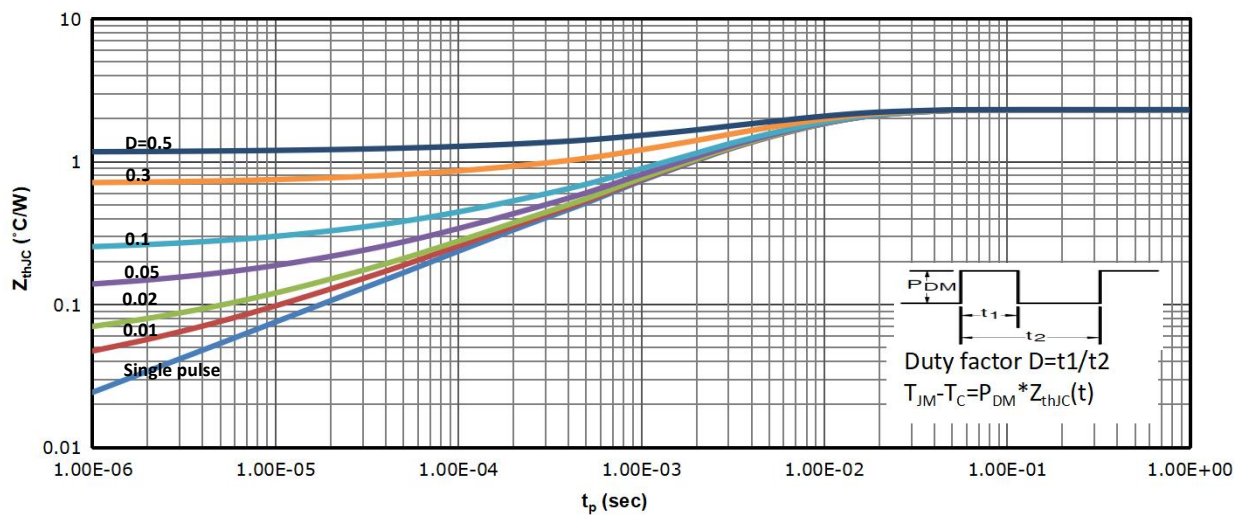
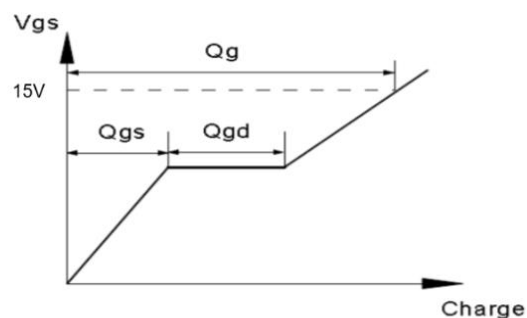


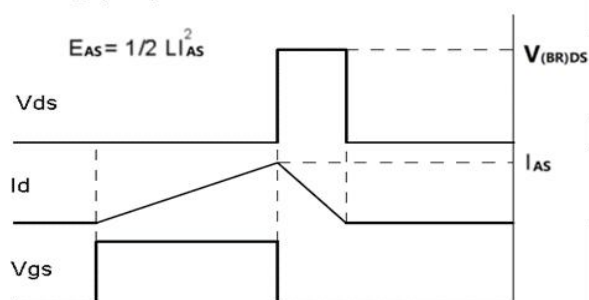
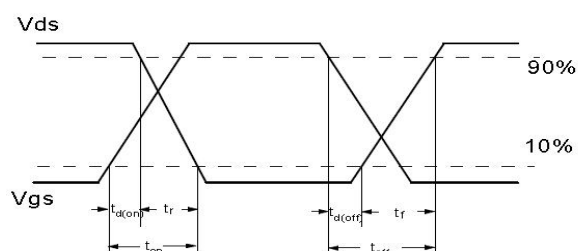
Fig 14: Max. Transient Thermal Impedance



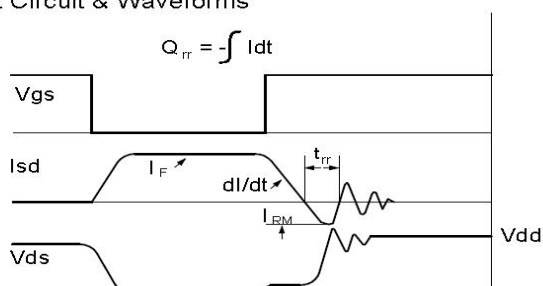
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



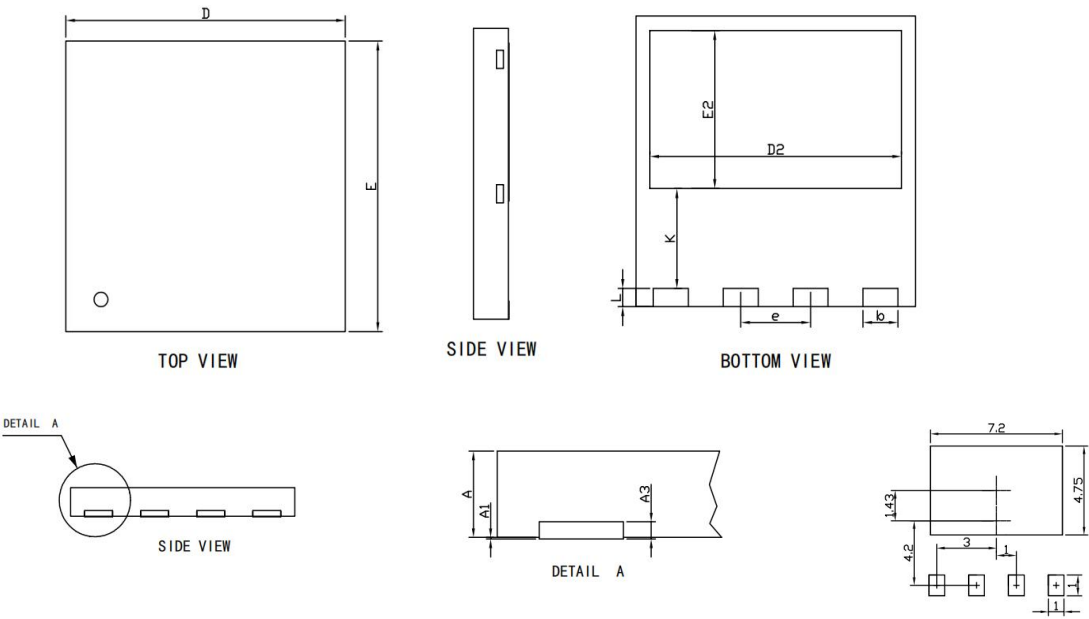
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Package Outline: DFN8*8



SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.90	1.10	0.035	0.043
A1	0.00	0.05	0.000	0.002
A3	0.20		0.008	
b	0.90	1.10	0.035	0.043
D	7.90	8.10	0.311	0.319
E	7.90	8.10	0.311	0.319
D2	7.10	7.30	0.280	0.287
E2	4.25	4.45	0.167	0.175
e	1.90	2.10	0.075	0.083
K	2.65	2.85	0.104	0.112
L	0.40	0.60	0.016	0.024

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